

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	670493	insulat\$3 dielectric	US-PGPUB; USPAT	OR	ON	2004/11/14 11:23
L2	566304	1 and (trench open\$3 hole via pattern)	US-PGPUB; USPAT	OR	ON	2004/11/14 11:24
L3	152753	2 and (copper Cu)	US-PGPUB; USPAT	OR	ON	2004/11/14 11:24
L4	18641	3 and (electroplat\$3 (electroless near5 plat\$3))	US-PGPUB; USPAT	OR	ON	2004/11/14 11:24
L5	14007	4 and etch\$3	US-PGPUB; USPAT	OR	ON	2004/11/14 11:29
L6	464	5 and (blind near5 via)	US-PGPUB; USPAT	OR	ON	2004/11/14 11:22
L7	13423	5 and metal\$8	US-PGPUB; USPAT	OR	ON	2004/11/14 11:20
L8	13427	5 and metal\$10	US-PGPUB; USPAT	OR	ON	2004/11/14 11:25
L9	5679	8 and interconnect	US-PGPUB; USPAT	OR	ON	2004/11/14 11:21
L10	3562	9 and wir\$3	US-PGPUB; USPAT	OR	ON	2004/11/14 11:21
L11	3482	10 and (substrate wafer)	US-PGPUB; USPAT	OR	ON	2004/11/14 11:21
L12	2973	11 and semiconductor	US-PGPUB; USPAT	OR	ON	2004/11/14 11:22
L13	1125	12 and (contact near3 pad)	US-PGPUB; USPAT	OR	ON	2004/11/14 11:22
L14	128	12 and (blind near5 via)	US-PGPUB; USPAT	OR	ON	2004/11/14 11:22
L15	1165	13 14	US-PGPUB; USPAT	OR	ON	2004/11/14 11:22
L17	300989	insulat\$3 dielectric	USOCR	OR	ON	2004/11/14 11:27
L18	228450	17 and (trench open\$3 hole via pattern)	USOCR	OR	ON	2004/11/14 11:27
L19	45661	18 and (copper Cu)	USOCR	OR	ON	2004/11/14 11:28
L20	1468	19 and (electroplat\$3 (electroless near5 plat\$3))	USOCR	OR	ON	2004/11/14 11:28
L21	566	20 and etch\$3	USOCR	OR	ON	2004/11/14 11:26
L22	29	21 and metallization	USOCR	OR	ON	2004/11/14 11:26
L23	1077872	insulat\$3 dielectric	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:27

L24	296567	23 and (trench open\$3 hole via pattern)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:28
L25	17207	24 and (copper Cu)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:28
L27	1271	25 and (electroplat\$3 (electroless near5 plat\$3))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:28
L28	510	27 and etch\$3	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:29